

# FQD2N100/FQU2N100

## 1000V N-Channel MOSFET

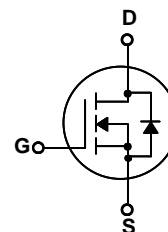
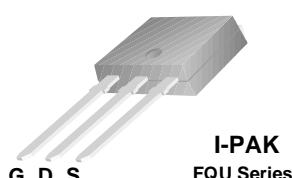
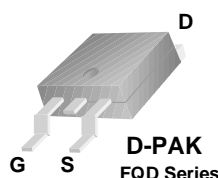
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for electronic lamp starter and ballast.

### Features

- 1.6A, 1000V,  $R_{DS(on)} = 9\Omega$  @  $V_{GS} = 10V$
- Low gate charge ( typical 12 nC)
- Low  $C_{rss}$  ( typical 5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQD2N100/FQU2N100	Units
$V_{DSS}$	Drain-Source Voltage	1000	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	1.6	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	1.0	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	6.4	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	160	mJ
$I_{AR}$	Avalanche Current (Note 1)	1.6	A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ ) *	2.5	W
	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	50	W
	- Derate above $25^\circ\text{C}$	0.4	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	2.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	$^\circ\text{C/W}$

\* When mounted on the minimum pad size recommended (PCB Mount)

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	1000	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.976	--	V/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 800\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

**On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 0.8\text{ A}$	--	7.1	9	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 0.8\text{ A}$ (Note 4)	--	1.9	--	S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	400	520	pF
$C_{oss}$	Output Capacitance		--	40	52	pF
$C_{rss}$	Reverse Transfer Capacitance		--	5	6.5	pF

**Switching Characteristics**

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 500\text{ V}, I_D = 2.0\text{ A},$ $R_G = 25\text{ }\Omega$  (Note 4, 5)	--	13	35	ns
$t_r$	Turn-On Rise Time		--	30	70	ns
$t_{d(off)}$	Turn-Off Delay Time		--	25	60	ns
$t_f$	Turn-Off Fall Time		--	35	80	ns
$Q_g$	Total Gate Charge	$V_{DS} = 800\text{ V}, I_D = 2.0\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	12	15.5	nC
$Q_{gs}$	Gate-Source Charge		--	2.5	--	nC
$Q_{gd}$	Gate-Drain Charge		--	6.5	--	nC

**Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		--	--	1.5	A
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current		--	--	6.0	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.6 A	--	--	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.0 A,	--	520	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs (Note 4)	--	2.3	--	μC

**Notes:**

1. Repetitive Rating ; Pulse width limited by maximum junction temperature
2.  $L = 120\text{ mH}, I_{AS} = 1.6\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 2.0\text{ A}, dI/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

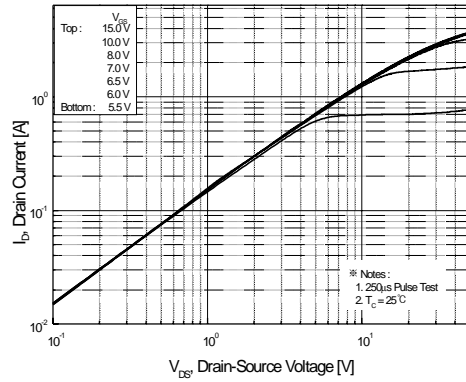


Figure 1. On-Region Characteristics

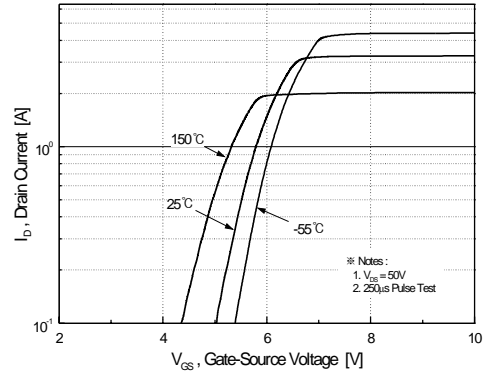


Figure 2. Transfer Characteristics

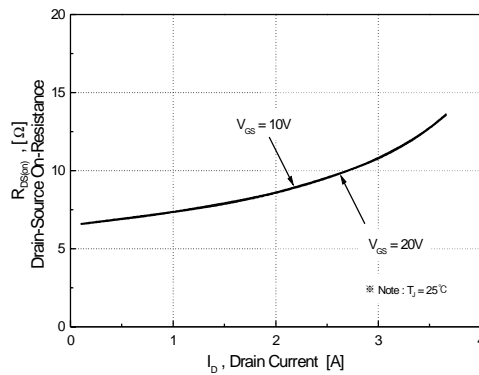


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

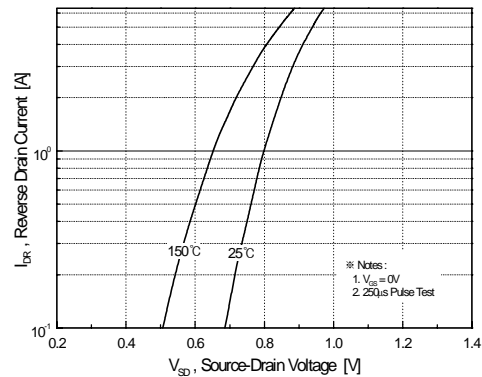


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

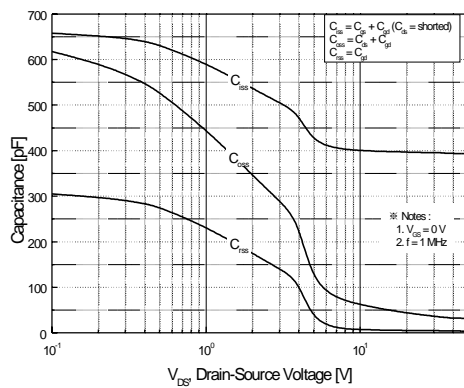


Figure 5. Capacitance Characteristics

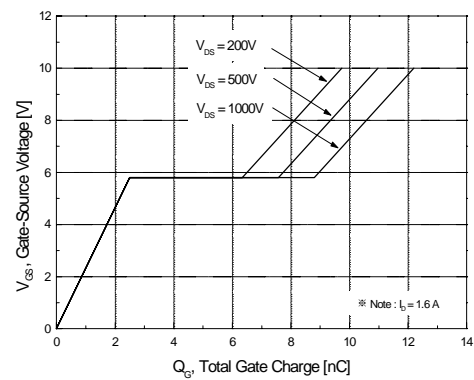


Figure 6. Gate Charge Characteristics

# Typical Characteristics (Continued)

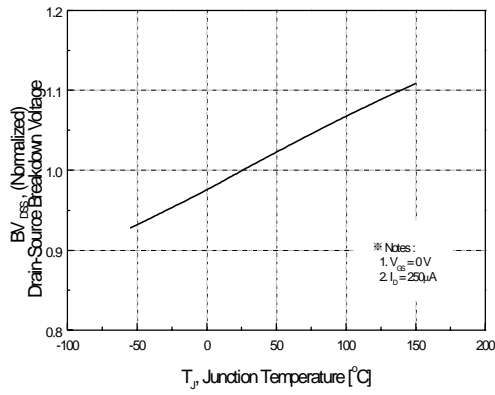


Figure 7. Breakdown Voltage Variation vs. Temperature

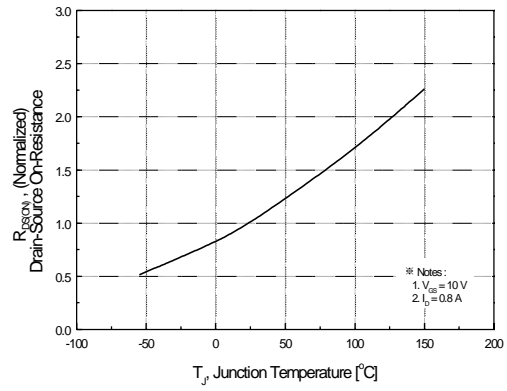


Figure 8. On-Resistance Variation vs. Temperature

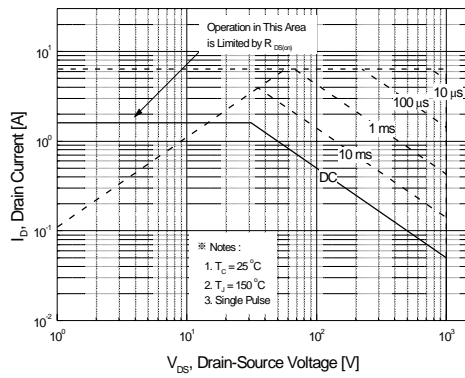


Figure 9. Maximum Safe Operating Area

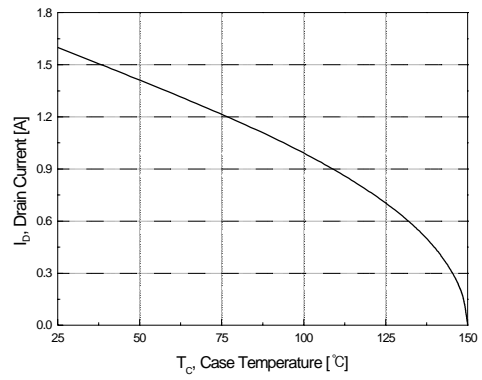


Figure 10. Maximum Drain Current vs. Case Temperature

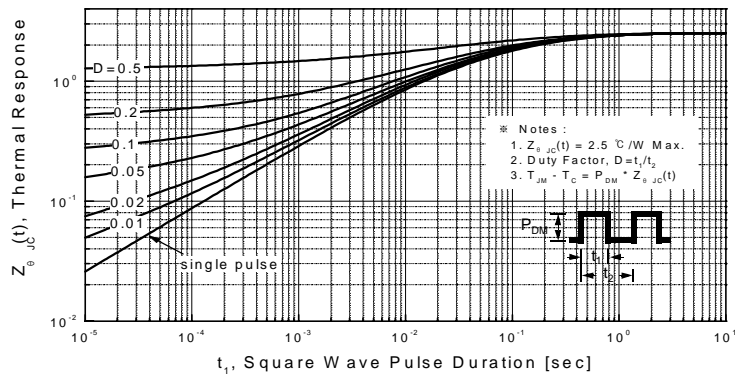
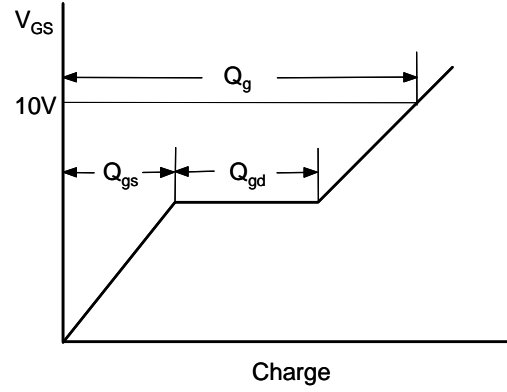
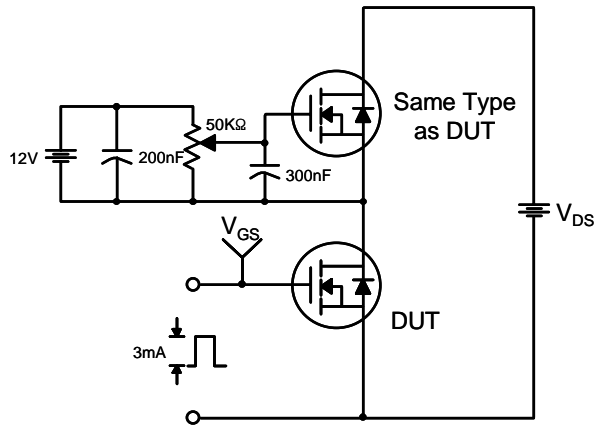
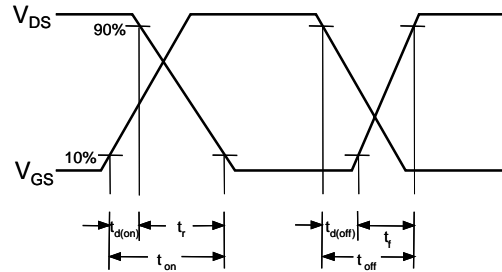
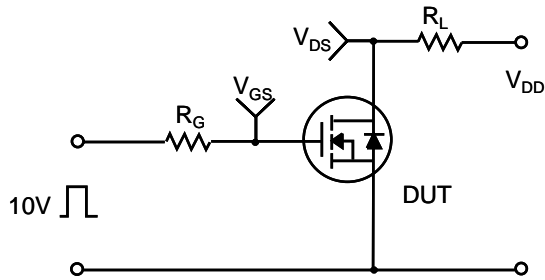


Figure 11. Transient Thermal Response Curve

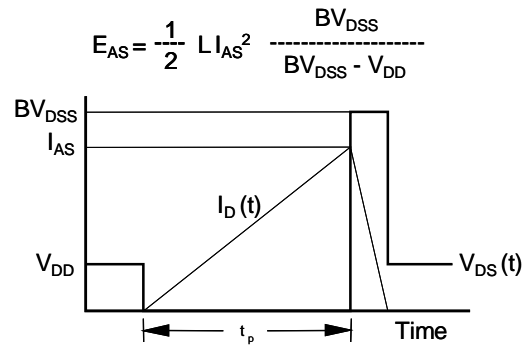
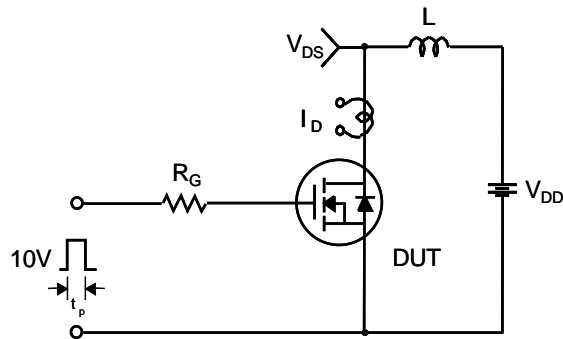
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms

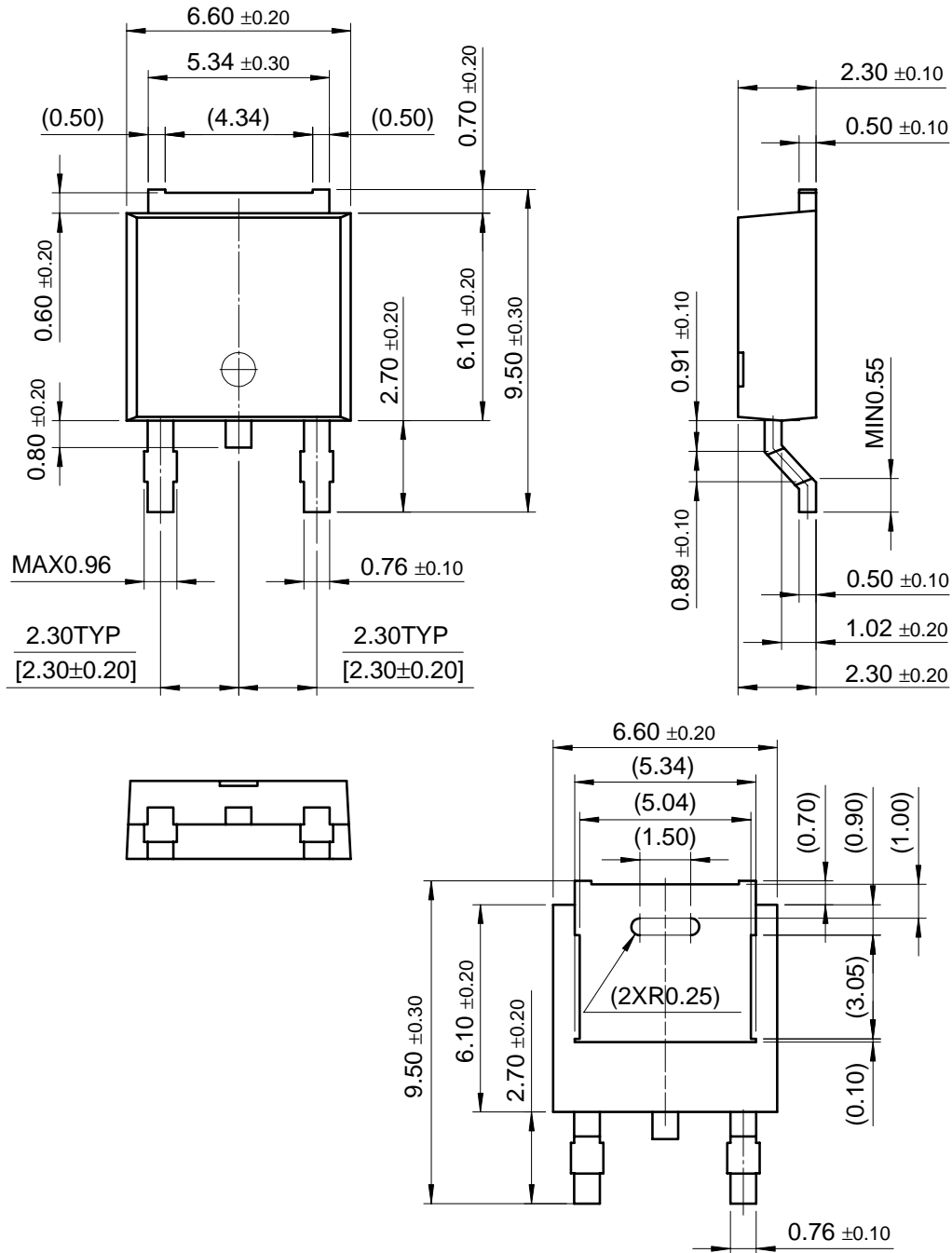


# Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

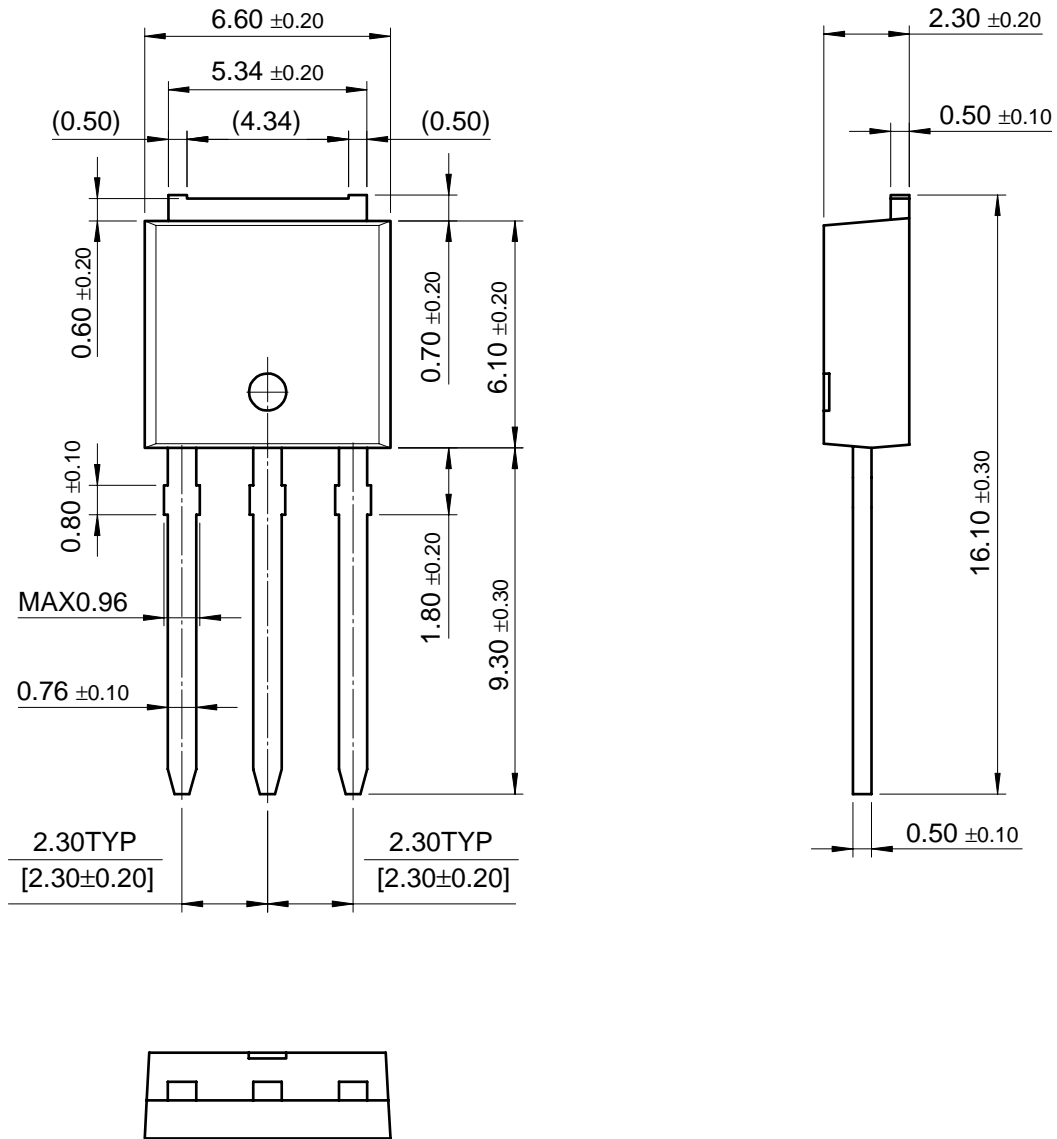
D-PAK



Dimensions in Millimeters

Package Dimension (Continued)

I-PAK



Dimensions in Millimeters



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